

# isc N-Channel MOSFET Transistor

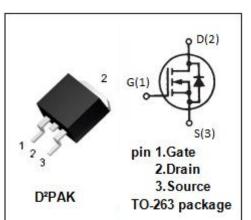
# PSMN2R2-40BS

### FEATURES

- Drain Current –I\_D= 100A@ T\_C=25 $^\circ\!\!\mathbb{C}$
- Drain Source Voltage-
  - : V<sub>DSS</sub>= 40V(Min)
- Static Drain-Source On-Resistance
- : R<sub>DS(on)</sub> = 2.2m Ω (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

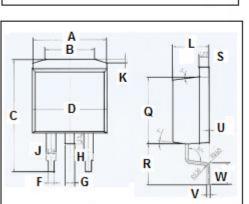
### DESCRIPTION

• Designed for use in switch mode power supplies and general purpose applications.



## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT		
V <sub>DSS</sub>	Drain-Source Voltage	40	V		
V <sub>GS</sub>	Gate-Source Voltage-Continuous	±20	V		
ID	Drain Current-Continuous	100	А		
I <sub>DM</sub>	Drain Current-Single Pluse	962	А		
P <sub>D</sub>	Total Dissipation @T <sub>c</sub> =25℃	306	W		
TJ	Max. Operating Junction Temperature	-55~175	°C		
T <sub>stg</sub>	Storage Temperature	-55~175	°C		



DIM	m	m
	MIN	MAX
A	1	0
В	6.6	6.8
С	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
Н	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
0	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	0.5	°C/W

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### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25\,^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA	40		V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 1mA	2.0	4.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 25A		2.2	mΩ
Igss	Gate-Body Leakage Current	V <sub>GS</sub> = ±16V;V <sub>DS</sub> =0		±100	nA
loss	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 40V; V <sub>GS</sub> = 0		10	μA
V <sub>SD</sub>	Forward On-Voltage	I <sub>S</sub> = 25A; V <sub>GS</sub> = 0		1.2	V

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